



P-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ)
-200	5.0 @ $V_{GS} = -10$ V	-0.38	4.1
	5.1 @ $V_{GS} = -6$ V	-0.37	

FEATURES

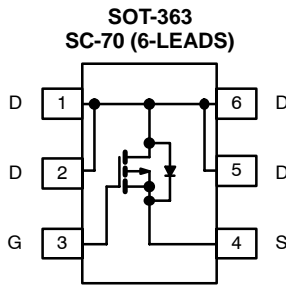
- TrenchFET® Power MOSFETS
- Small, Thermally Enhanced SC-70 Package
- Ultra Low On-Resistance



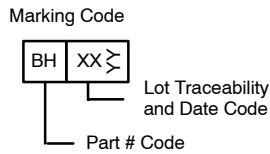
Pb-free
Available

APPLICATIONS

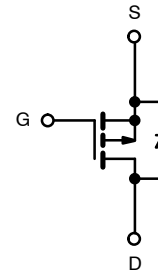
- Active Clamp Switch in DC/DC Power Supplies



Top View



Ordering Information: Si1419DH-T1—E3



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	5 secs	Steady State	Unit	
Drain-Source Voltage	V_{DS}	-200		V	
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	$T_A = 25^\circ\text{C}$	-0.38	-0.3	A
		$T_A = 85^\circ\text{C}$	-0.27	-0.22	
Pulsed Drain Current	I_{DM}	-0.5			
Continuous Diode Current (Diode Conduction) ^a	I_S	-1.3	-0.83		
Single Pulse Avalanche Current	$L = 0.1$ mH	I_{AS}	-1.9		
Single Pulse Avalanche Energy		E_{AS}	0.18		mJ
Maximum Power Dissipation ^a	P_D	$T_A = 25^\circ\text{C}$	1.56	1.0	W
		$T_A = 85^\circ\text{C}$	0.81	0.52	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 5$ sec	60	80	$^\circ\text{C/W}$
		Steady State	100	125	
Maximum Junction-to-Foot (Drain)	R_{thJF}	34	45		

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

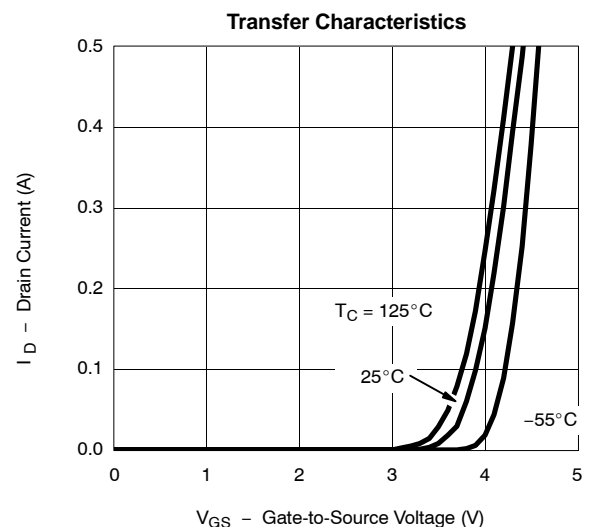
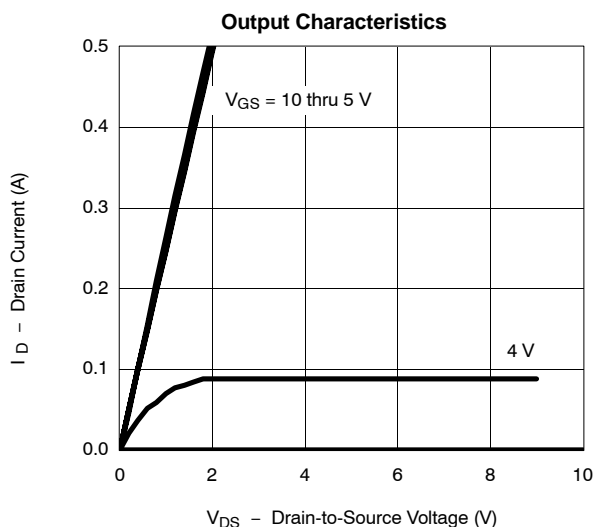

SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -100 μA	-2.5		-4.5	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -200 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -200 V, V _{GS} = 0 V, T _J = 85 °C			-5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = -15 V, V _{GS} = -10 V	-0.5			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = -10 V, I _D = -0.4 A		3.98	5.0	Ω
		V _{GS} = -6 V, I _D = -0.4 A		4.06	5.1	
Forward Transconductance ^a	g _{fs}	V _{DS} = -10 V, I _D = -0.4 A		1.0		S
Diode Forward Voltage ^a	V _{SD}	I _S = -0.4 A, V _{GS} = 0 V		-0.80	-1.1	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = -100 V, V _{GS} = -10 V, I _D = -0.4 A		4.1	6.2	nC
Gate-Source Charge	Q _{gs}			0.8		
Gate-Drain Charge	Q _{gd}			1.3		
Gate Resistance	R _g	f = 1.0 MHz		17		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = -100 V, R _L = 100 Ω I _D ≅ -1 A, V _{GEN} = -4.5 V, R _g = 6 Ω		6	9	ns
Rise Time	t _r			12	18	
Turn-Off Delay Time	t _{d(off)}			12	18	
Fall Time	t _f			12	18	
Reverse Recovery Time	t _{rr}	I _F = -0.4 A, di/dt = 100 A/μs		55	83	ns
Body Diode Reverse Recovery Charge	Q _{rr}			130	200	

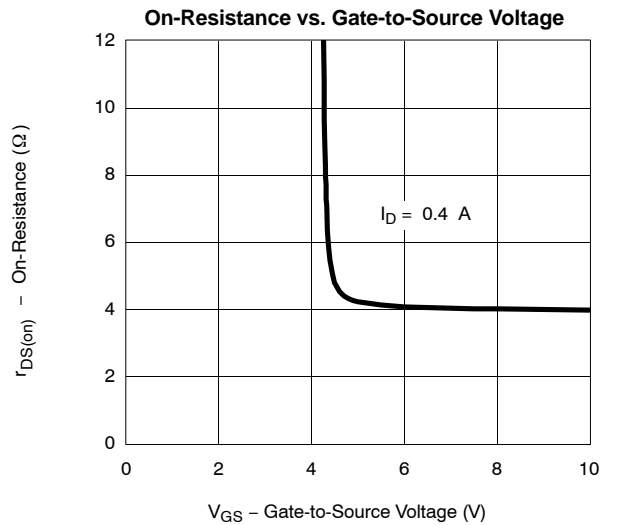
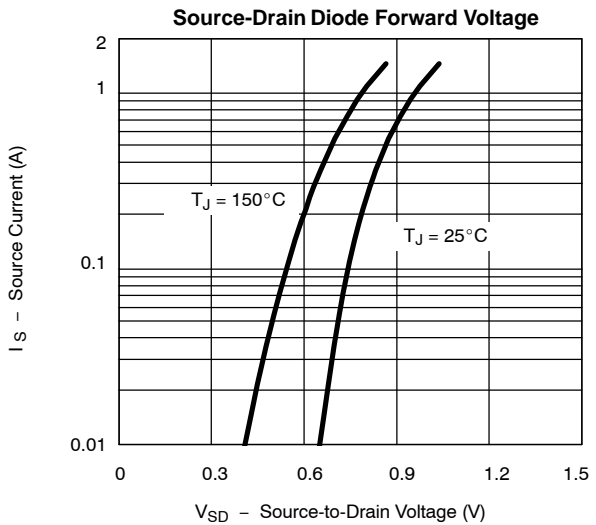
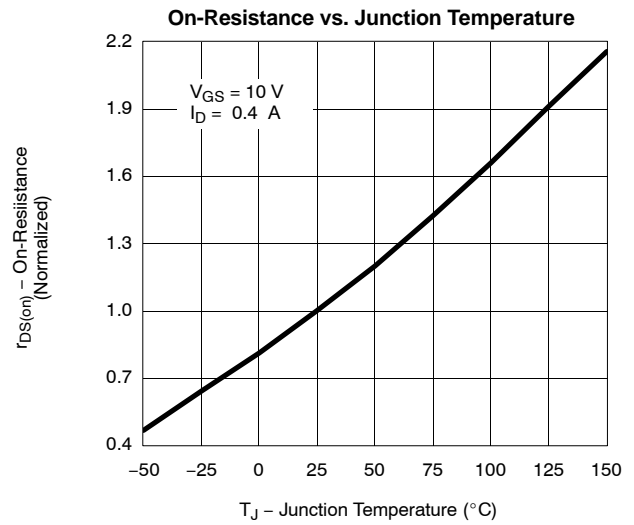
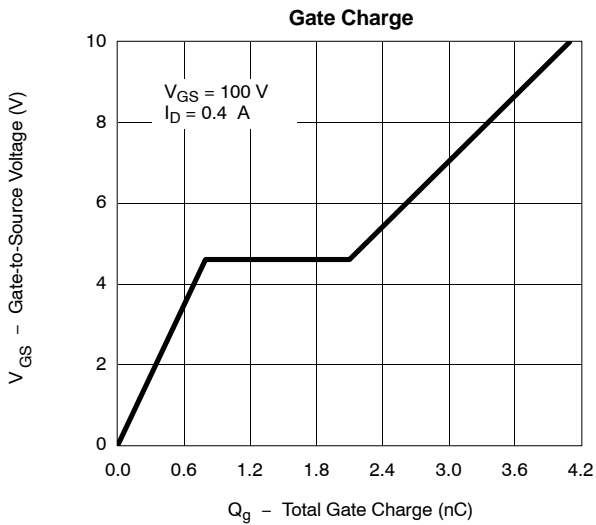
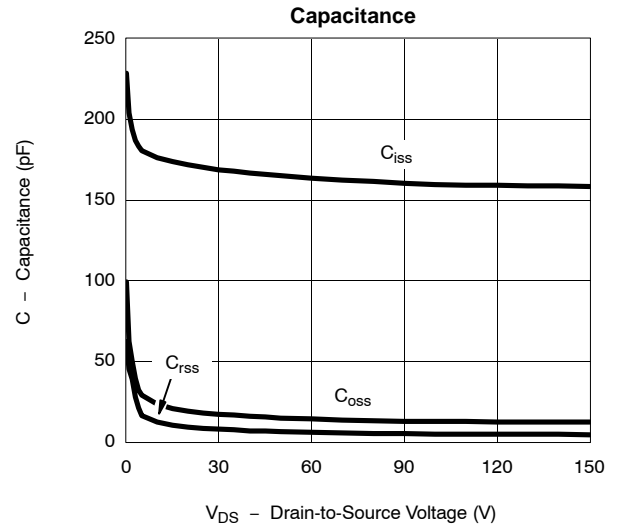
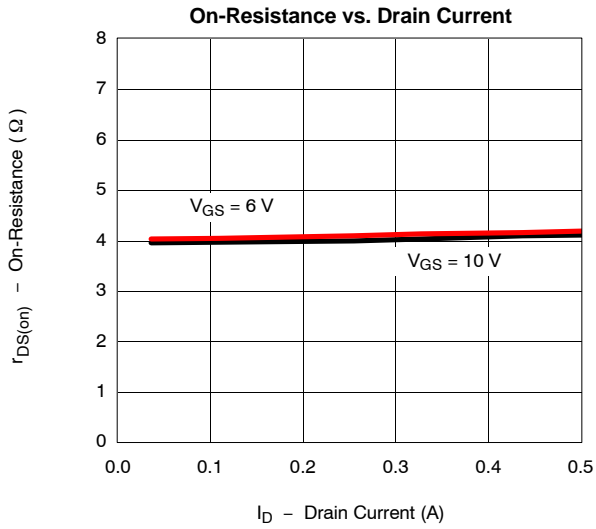
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

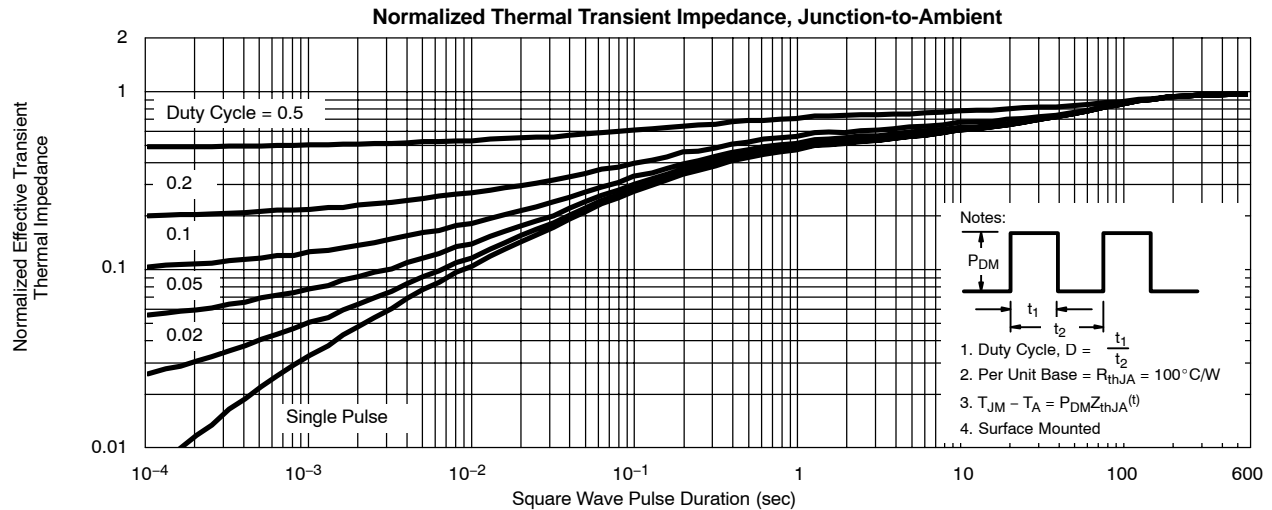
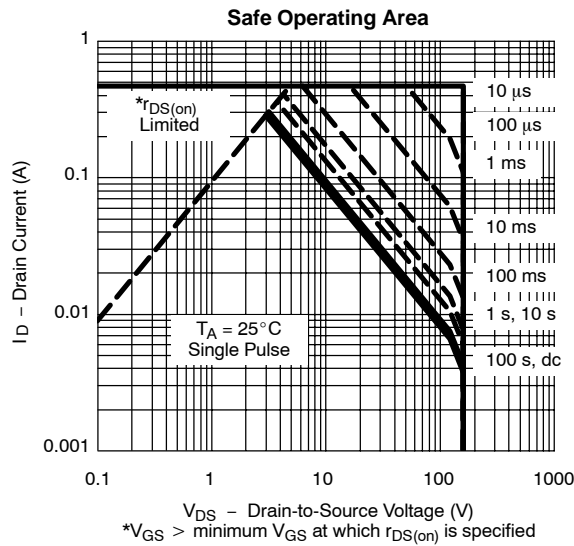
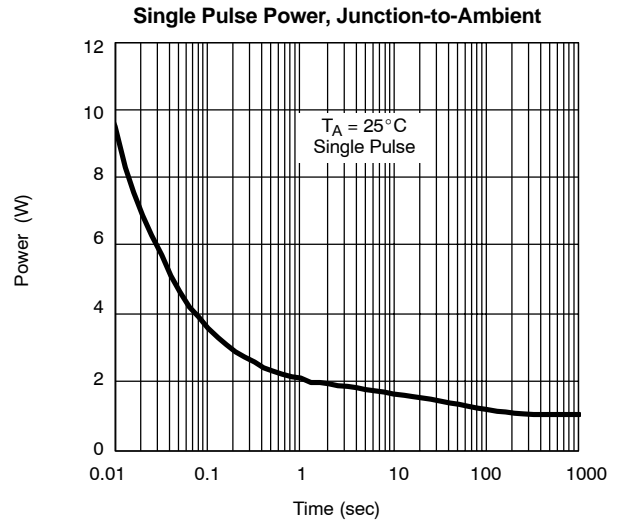
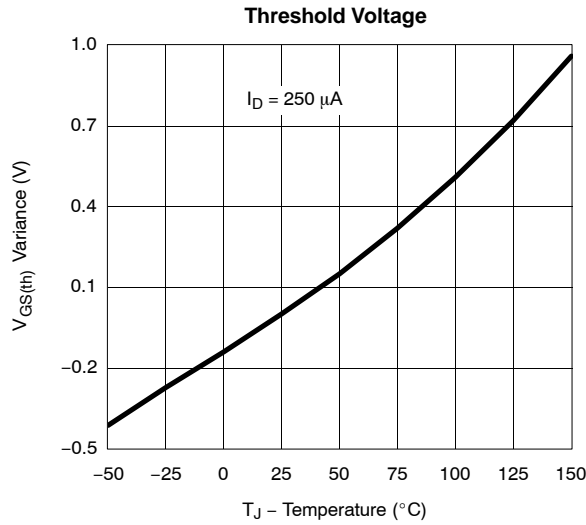
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)


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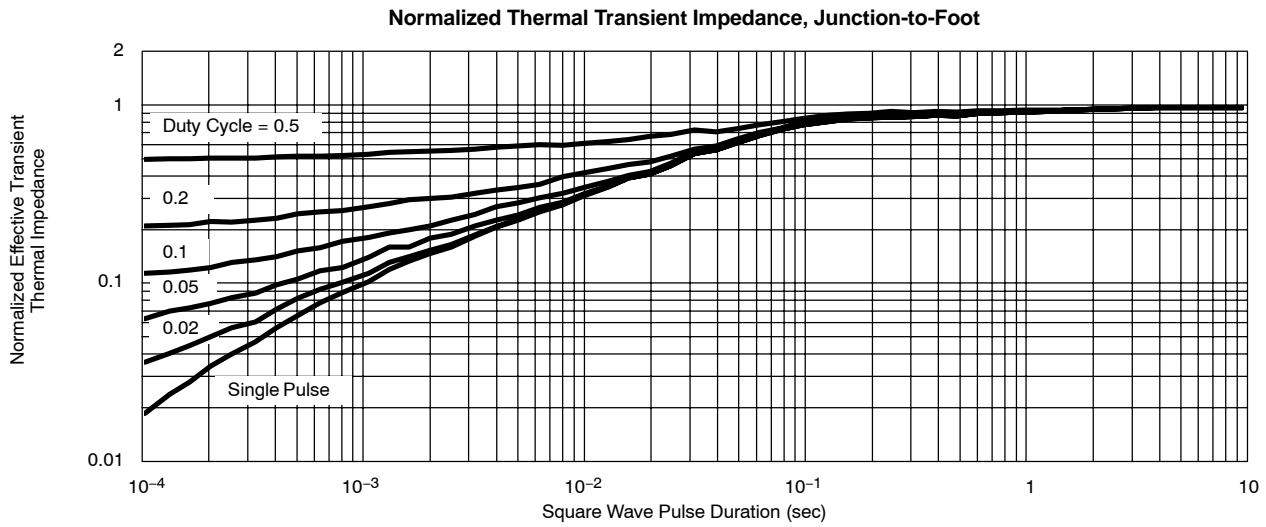


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